
Silicon Nitride, Silicon Dioxide, and Emerging Dielectrics 10

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Sponsoring Division:



Dielectric Science & Technology



Published by

The Electrochemical Society

65 South Main Street, Building D
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

www.electrochem.org

ecstransactions™

Vol. 19 No. 2

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)

ISBN 978-1-56677-710-0 (Hardcover)
ISBN 978-1-60768-060-4 (PDF)

Printed in the United States of America.

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